

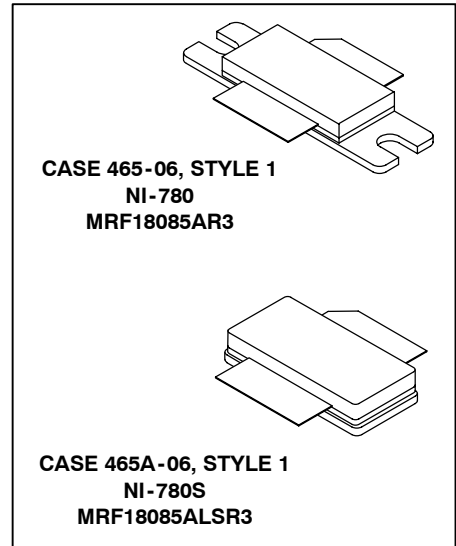
The RF MOSFET Line
RF Power Field Effect Transistors
N-Channel Enhancement-Mode Lateral MOSFETs

MRF18085AR3
MRF18085ALSR3

Designed for GSM and GSM EDGE base station applications with frequencies from 1.8 to 2.0 GHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications. Specified for GSM-GSM EDGE 1805 - 1880 MHz.

- GSM and GSM EDGE Performance, Full Frequency Band (1805-1880 MHz)
 Power Gain - 15 dB (Typ) @ 85 Watts CW
 Efficiency - 52% (Typ) @ 85 Watts CW
- Internally Matched, Controlled Q, for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 5:1 VSWR, @ 26 Vdc, @ P1dB Output Power, @ f = 1805 MHz
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Available with Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ" Nominal.
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

GSM/GSM EDGE
1.8 - 1.88 GHz, 85 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFETs



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	65	Vdc
Gate-Source Voltage	V _{GS}	-0.5, +15	Vdc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	273 1.56	Watts W/°C
Storage Temperature Range	T _{stg}	- 65 to +150	°C
Operating Junction Temperature	T _J	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value (1)	Unit
Thermal Resistance, Junction to Case	R _{θJC}	0.79	°C/W

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)

(1) Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.motorola.com/semiconductors/rf>. Select Documentation/Application Notes - AN1955.

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 100 μAdc)	V _{(BR)DSS}	65	—	—	Vdc
Zero Gate Voltage Drain Current (V _{DS} = 26 Vdc, V _{GS} = 0 Vdc)	I _{DSS}	—	—	10	μAdc
Gate-Source Leakage Current (V _{GS} = 5 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	—	—	1	μAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = 10 Vdc, I _D = 200 μAdc)	V _{GS(th)}	2	—	4	Vdc
Gate Quiescent Voltage (V _{DS} = 26 Vdc, I _D = 600 mAdc)	V _{GS(Q)}	2.5	3.9	4.5	Vdc
Drain-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 2 Adc)	V _{DS(on)}	—	0.15	—	Vdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 2 Adc)	g _{fs}	—	6.0	—	S

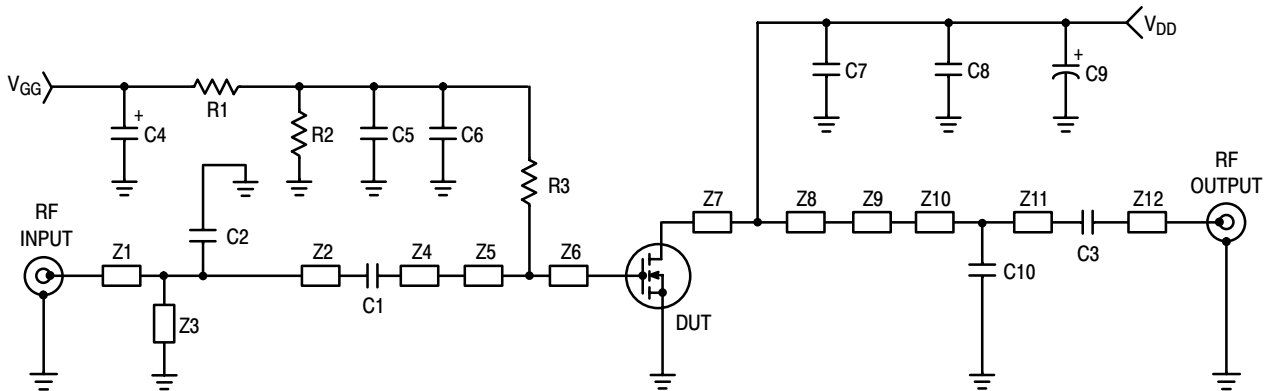
DYNAMIC CHARACTERISTICS

Reverse Transfer Capacitance (1) (V _{DS} = 26 Vdc, V _{GS} = 0, f = 1 MHz)	C _{rss}	—	3.6	—	pF
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FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system)

Common-Source Amplifier Power Gain @ 85 W (2) (V _{DD} = 26 Vdc, I _{DQ} = 800 mA, f = 1805 - 1880 MHz)	G _{ps}	13.5	15	—	dB
Drain Efficiency @ 85 W (2) (V _{DD} = 26 Vdc, I _{DQ} = 800 mA, f = 1805 - 1880 MHz)	η	48	52	—	%
Input Return Loss @ 85 W (2) (V _{DD} = 26 Vdc, I _{DQ} = 800 mA, f = 1805 - 1880 MHz)	IRL	—	-12	-9	dB
Power Output, 1 dB Compression Point (V _{DD} = 26 Vdc, I _{DQ} = 800 mA, f = 1805 - 1880 MHz)	P1dB	83	90	—	Watts
Output Mismatch Stress @ P1dB (V _{DD} = 26 Vdc, I _{DQ} = 800 mA, f = 1805 MHz, VSWR = 5:1, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power Before and After Test			

- (1) Part is internally matched both on input and output.
 (2) To meet application requirements, Motorola test fixtures have been designed to cover the full GSM1800 band, ensuring batch-to-batch consistency.



C1, C3, C6, C7	10 pF Chip Capacitors, B Case, ATC	Z4	0.610" x 0.118" Microstrip
C2	1.8 pF Chip Capacitor, B Case, ATC	Z5	0.331" x 1.153" Microstrip
C4	10 μ F, 35 V Tantalum Capacitor, AVX	Z6	0.063" x 1.153" Microstrip
C5, C8	1 nF Chip Capacitors, B Case, ATC	Z7	0.122" x 0.925" Microstrip
C9	220 μ F, 63 V Electrolytic Capacitor, Radial, Philips	Z8	0.547" x 0.925" Microstrip
C10	0.3 pF Chip Capacitor, B Case, ATC	Z9	0.394" x 0.177" Microstrip
R1, R2	10 k Ω , 1/4 W Chip Resistors (1206)	Z10	0.180" x 0.087" Microstrip
R3	1.0 k Ω , 1/4 W Chip Resistor (1206)	Z11	0.686" x 0.087" Microstrip
Z1	0.671" x 0.087" Microstrip	Z12	0.294" x 0.087" Microstrip
Z2	0.568" x 0.087" Microstrip	PCB	Taconic TLX8, 30 mils, $\epsilon_r = 2.55$
Z3	0.500" x 0.098" Microstrip Shorted Stub		

Figure 1. 1.80 - 1.88 GHz Test Fixture Schematic

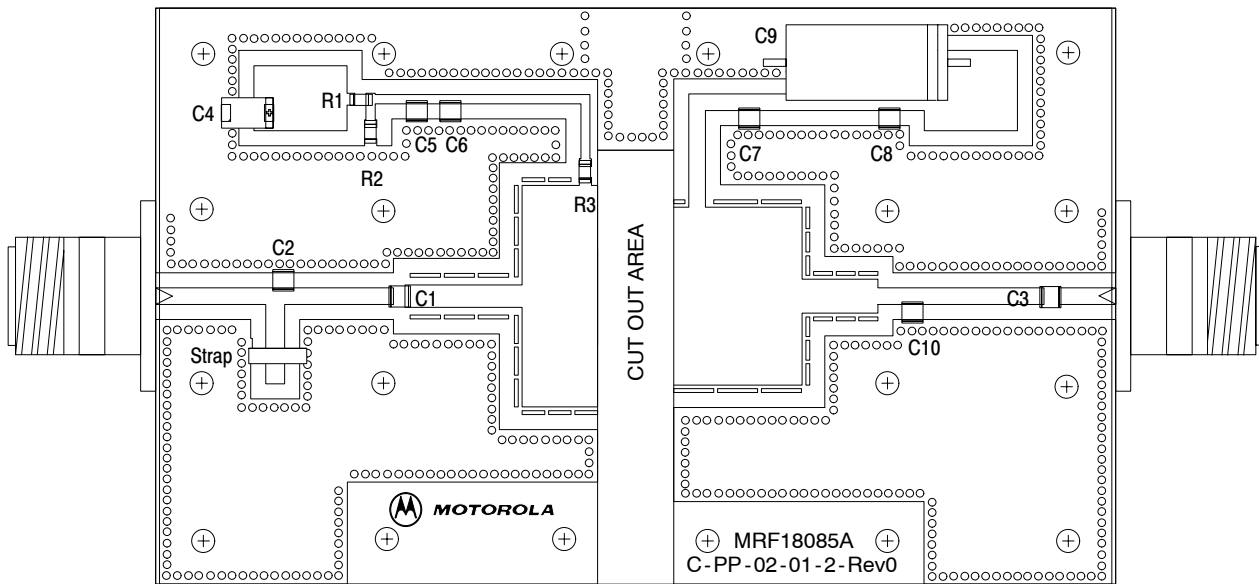


Figure 2. 1.80 - 1.88 GHz Test Fixture Component Layout

TYPICAL CHARACTERISTICS

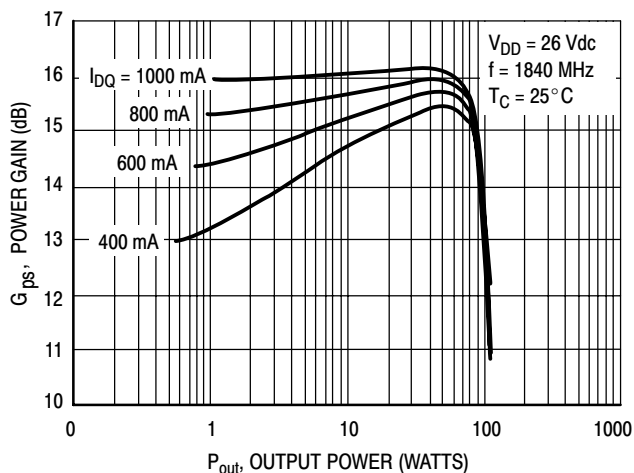


Figure 3. Power Gain versus Output Power

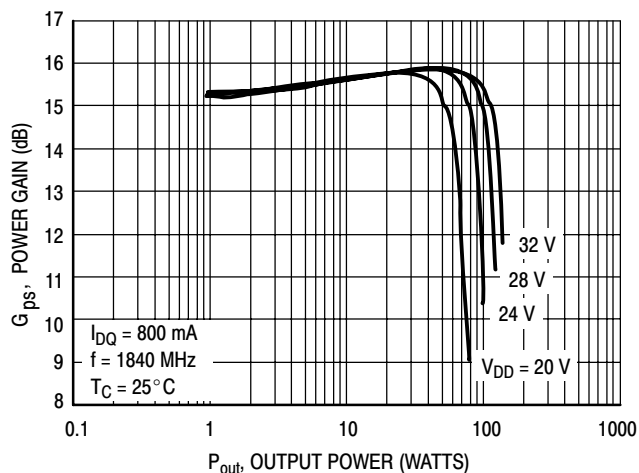


Figure 4. Power Gain versus Output Power

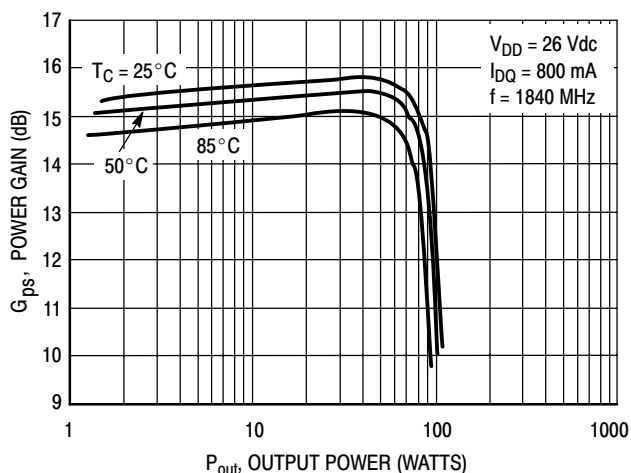


Figure 5. Power Gain versus Output Power

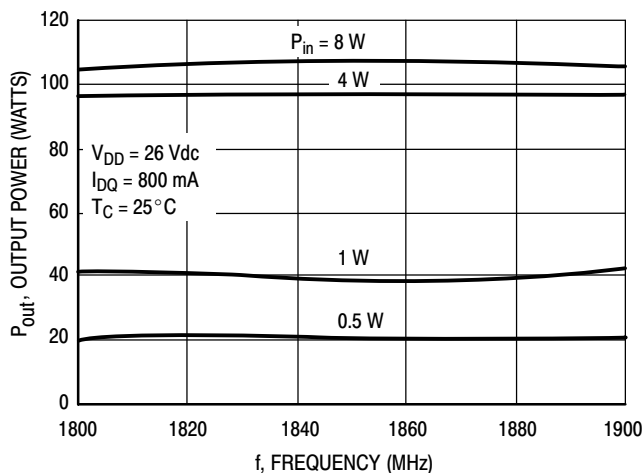


Figure 6. Output Power versus Frequency

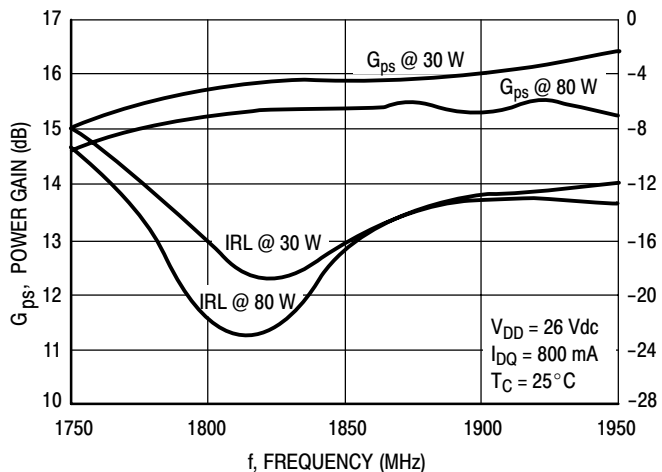


Figure 7. Power Gain versus Frequency

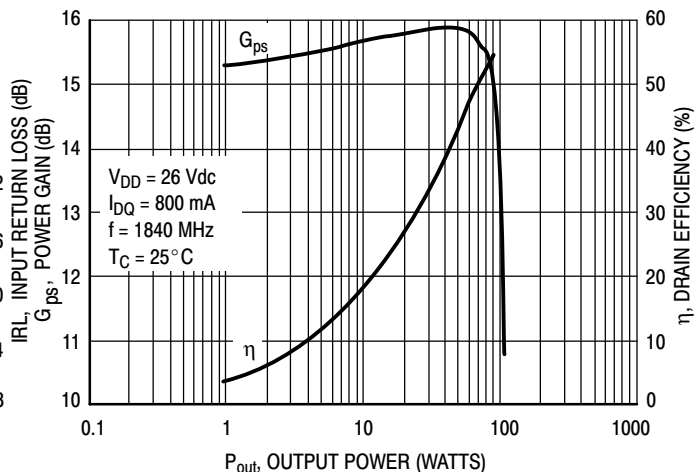
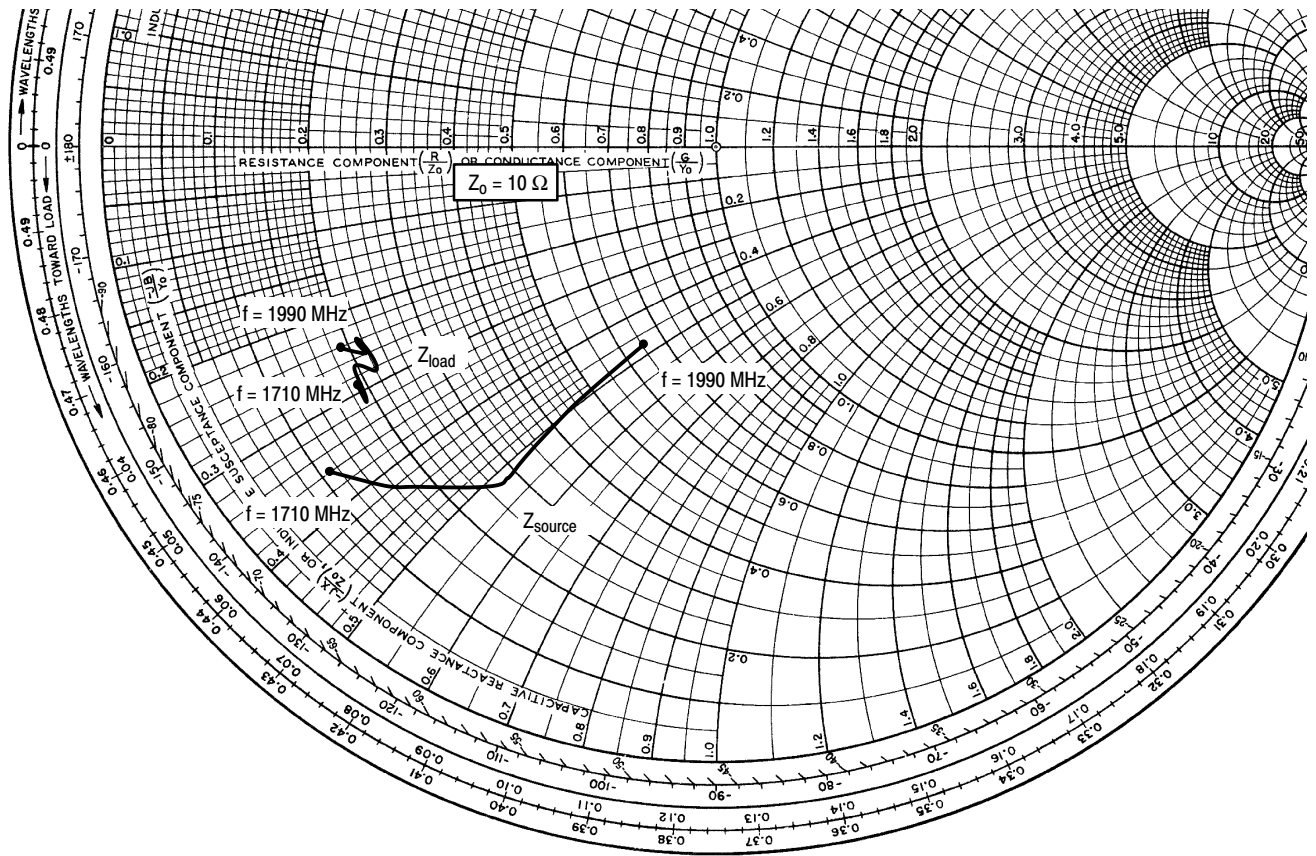


Figure 8. Power Gain and Efficiency versus Output Power



$V_{DD} = 26 \text{ V}$, $I_{DQ} = 800 \text{ mA}$, $P_{out} = 85 \text{ W CW}$

f MHz	Z_{source} Ω	Z_{load} Ω
1710	1.13 - j3.62	1.79 - j2.88
1785	1.61 - j4.23	1.82 - j3.15
1805	1.69 - j4.34	1.90 - j2.66
1880	2.83 - j5.25	2.09 - j2.77
1930	3.00 - j5.18	2.01 - j2.44
1960	4.39 - j4.97	2.01 - j2.57
1990	6.59 - j4.74	1.79 - j2.37

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

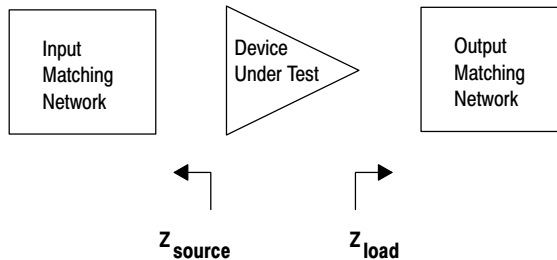


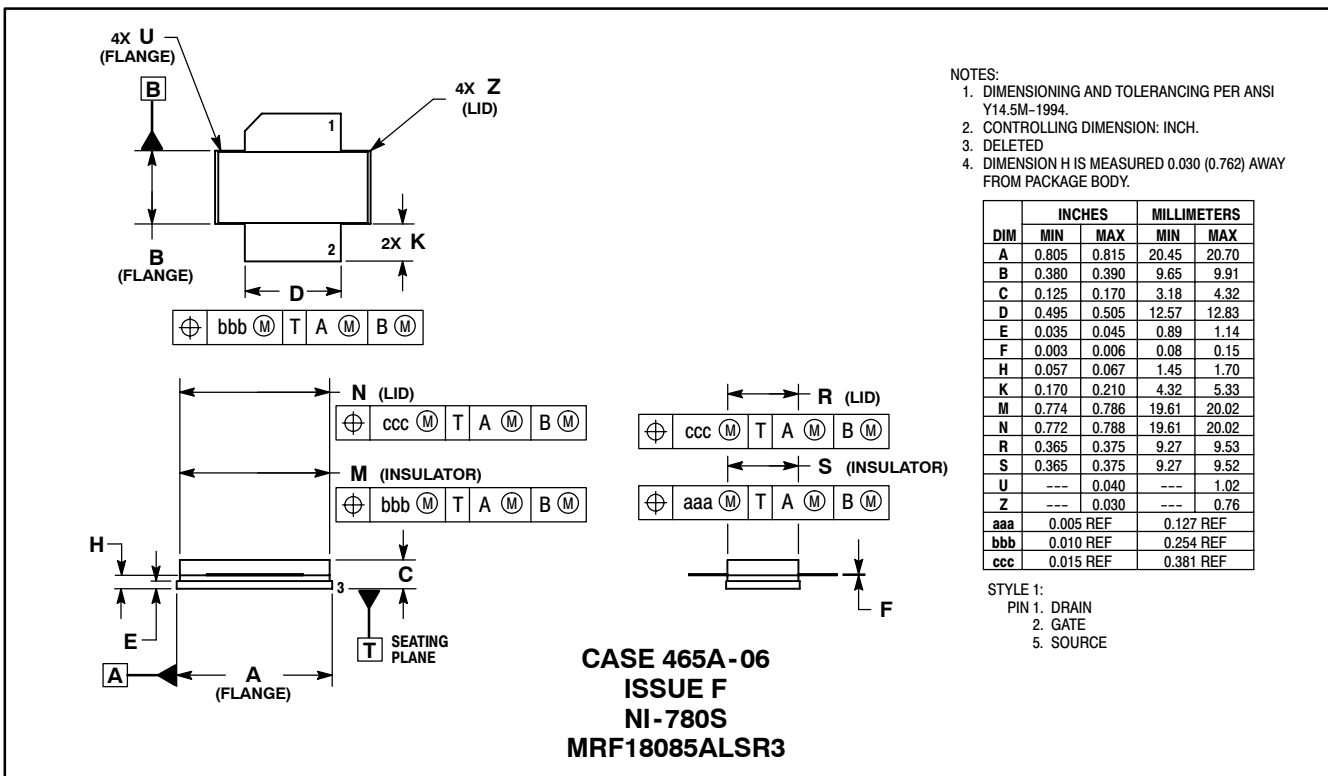
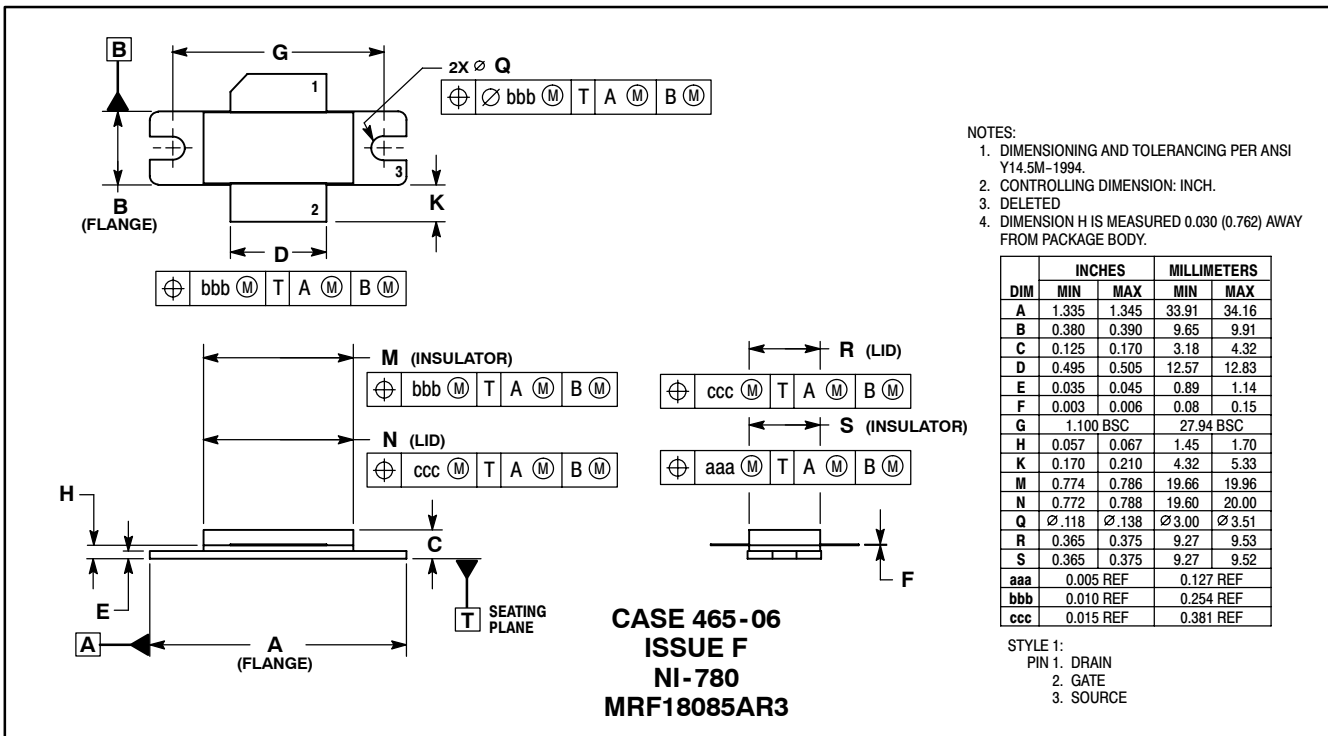
Figure 9. Series Equivalent Input and Output Impedance

NOTES

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PACKAGE DIMENSIONS

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JAPAN: Motorola Japan Ltd.; SPS, Technical Information Center,
3-20-1, Minami-Azabu, Minato-ku, Tokyo 106-8573, Japan
81-3-3440-3569

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Centre,
2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong
852-26668334

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